TOSHIBA Transistor Silicon NPN Triple Diffused Type

# 2SD2462

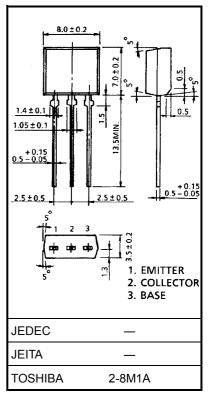
### **Power Amplifier Applications**

Unit: mm

- High DC current gain:  $h_{FE}$  (1) = 800 to 3200 ( $V_{CE}$  = 5 V,  $I_{C}$  = 0.2 A)
- Low saturation voltage:  $V_{CE (sat)} = 0.4 \text{ V (typ.)} (I_{C} = 1 \text{ A}, I_{B} = 10 \text{ mA})$
- Complementary to 2SB1602

### **Maximum Ratings (Ta = 25°C)**

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		$V_{CBO}$	60	V	
Collector-emitter voltage		V <sub>CEO</sub>	60	V	
Emitter-base voltage		V <sub>EBO</sub>	7	V	
Collector current	DC	IC	3	Α	
	Pulse	I <sub>CP</sub>	6		
Base current		I <sub>B</sub>	0.6	Α	
Collector power dissipation		PC	1.3	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	−55 to 150	°C	

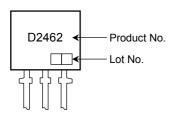


Weight: 0.55 g (typ.)

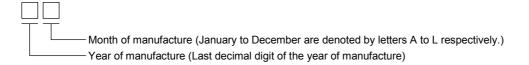
# Electrical Characteristics (Ta = 25°C)

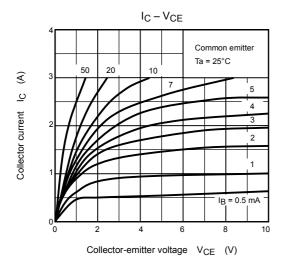
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0	_	_	100	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 7 V, I <sub>C</sub> = 0	_	_	100	μA
Collector-emitter breakdown voltage	V (BR) CEO	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0	60	_	_	V
DC current gain	h <sub>FE (1)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.2 A	800	_	3200	
	h <sub>FE (2)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 1.5 A	350	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 10 mA	_	0.4	1.0	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 A	_	0.7	1.0	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 A	_	18	_	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	42	_	pF

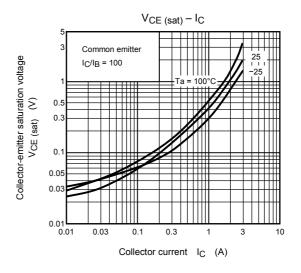
## Marking

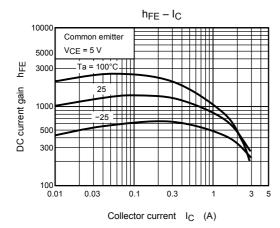


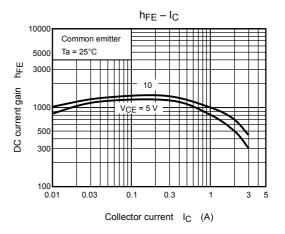
# **Explanation of Lot No.**

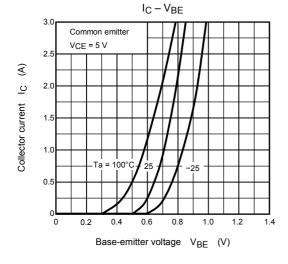


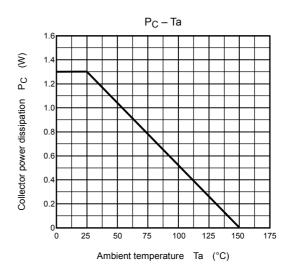




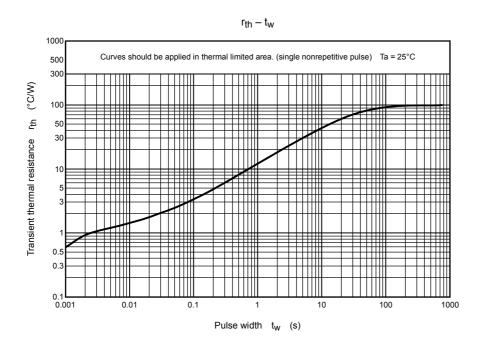


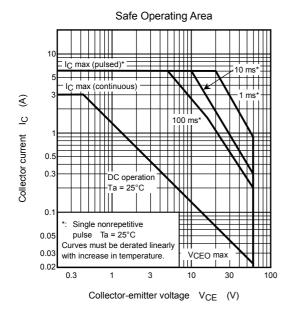






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